

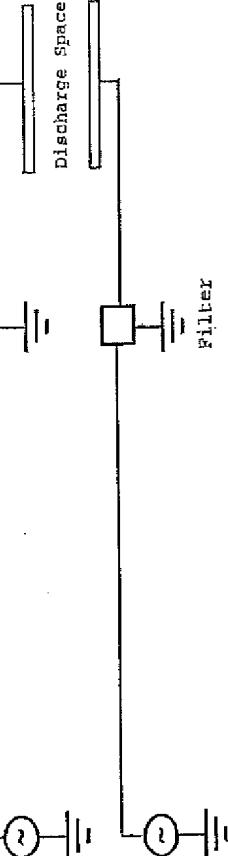
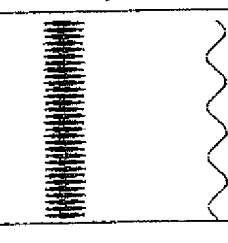
Correspondence Table 1-1

	The present Application	Priority Document JP2003-197799
Claims 1-3	an atmospheric pressure plasma processing apparatus at atmospheric pressure or at approximately	[0001], [0022]
	(i) high frequency electric field A is formed by superposing a first high frequency electric field and a second high frequency electric field	Claim 7, [0007], [0027], [0035] - [0041]
	(i) a first high frequency electric field of 200 kHz or less and a second high frequency electric field of 800 kHz or more	[0039] - [0040]
	(ii) transferring energy of the excited discharge gas to a film forming gas, whereby the film forming gas is excited;	[0023]
	the first process comprising the steps of:	
	(iii) exposing a substrate to the excited film forming gas, whereby a film is formed on the substrate,	Claim 1 [0014] - [0015] Example 1 [0056] - [0058]
	the second process comprising the steps of:	
	(v) exposing the film formed in the first process to the excited gas containing the oxidizing gas,	
	moving the substrate between the first discharge space and the second discharge space	Claim 2, [0032], FIG.1, FIG.2
	the discharge gas contains nitrogen of which content is 50 % by volume or more based on a volume of the discharge gas	Example 1 [0057], Example 2 [0072] film forming gas: 11 (=10+1) L/minute (21.1%) discharge gas: nitrogen 40 L/minute (76.9%)
Claim 4	a discharge space of the first process is formed between a first electrode and a second electrode which are facing each other;	[0007], [0031], FIG. 1, FIG. 2, FIG. 3
	the first high frequency electric field is applied by the first electrode and the second high frequency electric field is applied by the second electrode	[0037], FIG. 2
Claim 4	the discharge gas contains a reducing gas	Example 1 [0057], Example 2 [0072] reducing gas: hydrogen 1 L/minute (1.9%)
	the reducing gas is hydrogen	Example 1 [0057], Example 2 [0072]

Correspondence Table 1-2

	The present Application	Priority Document JP2003-197799
Claim 12	the film is a metal oxide film	Example 1 [0057], Example 2 [0072]
Claim 13	the film is a transparent conductive film	Example 1, [0069], Table 2, Example 2 [0072]
Claim 14	the film forming gas contains an organo-metallic compound having a metal atom selected from the group consisting of indium(In), tin(Sn), zinc(Zn), zirconium(Zr), antimony(Sb), aluminum(Al), gallium(Ga) and germanium(Ge)	Example 1 [0057], Example 2 [0072] In, Sn
Claim 15	the first process and the second process are alternately repeated a plurality of times	Claim 2, Example 1 [0058]
Claim 16	a thickness of the accumulated film in the first process per batch is not more than 10 nm	Claim 4, [0018], Example 1 [0058] - [0063]
Figures	FIG. 1 FIG. 2(a), FIG. 2(b)	FIG. 1 + FIG. 2 FIG. 3(a), FIG. 3(b)

Comparison between the Present Application and Suemasa Reference

	Pressure	Gas	Applied Wave Form	Power Supply Mechanism	Electric Field in Discharge Space
Present Application II 10/544,084	At or near atmospheric pressure (20 - 110 kPa)	Discharge Gas: Nitrogen > 50 volume %			
Reference Suemasa 6,089,181	Reduced pressure atmosphere (ex. 20 mTorr)	Gas: CAFB	